

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device including: a semiconductor substrate; at least one layer of a first insulating film formed above the semiconductor substrate and having a relative dielectric constant of 3.8 or less, an entire layer of the first insulating film being separated at least near four corners of the semiconductor substrate by a lacking portion that extends along the four corners; and a second insulating film covering a side face of the entire layer of the first insulating film in the lacking portion on a center side of the semiconductor substrate and having a relative dielectric constant of over 3.8.